

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprises a base substrate,
an insulating film formed on the substrate, an undoped
first and lattice-relaxed semiconductor layer formed on
5 the insulating film, a second semiconductor layer
having a tensile strain and formed on the first
semiconductor layer, and a MISFET formed on the second
semiconductor layer. Since the MISFET is formed in
a strained Si layer, electrons are prevented from
10 scattering in a channel region, improving the electron
mobility. Furthermore, since the MISFET is formed in
a thin SOI layer having a thickness of 100 nm or less,
it is possible to reduce a parasitic capacitance in
addition to the improvement of the electron mobility.
15 As a result, the MISFET excellent in drivability can be
obtained.